



Rev.A.1.1

TEL

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I _{GT}	V _D =12V R _L =33Ω	- -	MAX.	5	mA
				10	
V _{GT}		ALL	MAX.	1	V
V _{GD}	V _D =V _{DRM} T _j =125 R _L =3.3kΩ	ALL	MIN.	0.2	V
I _L	I _G =1.2I _{GT}	- -	MAX.	15	mA
				20	
I _H	I _T =500mA		MAX.	10	mA
dV/dt	V _D =540V Gate Open T _j =125		MIN.	40	V/μs
(dV/dt) _c	(dI/dt) _c =5A/ms, T _j =110		MIN.	2	V/μs
t _{on}	I _G =20mA I _A =200mA I _R =20mA T _j =25		TYP.	3	μs
t _{off}				30	

Symbol	Parameter		Value(MAX.)	Unit
V _{TM}	I _{TM} =15A t _p =380μs	T _j =25	1.6	V
V _{TO}	Threshold voltage	T _j =125	0.8	V
R _D	Dynamic resistance	T _j =125	41	mΩ
I _{DRM}	V _D =V _{DRM} V _R =V _{RDM}	T _j =25	5	μA
I _{RRM}		T _j =125	0.4	mA

Symbol	Parameter	Value	Unit
R _{th(j-c)}	junction to case (AC)	1.5	/W
R _{th(j-a)}	junction to ambient (AC)	60	/W

FIG.1: Maximum power dissipation versus RMS on-state current

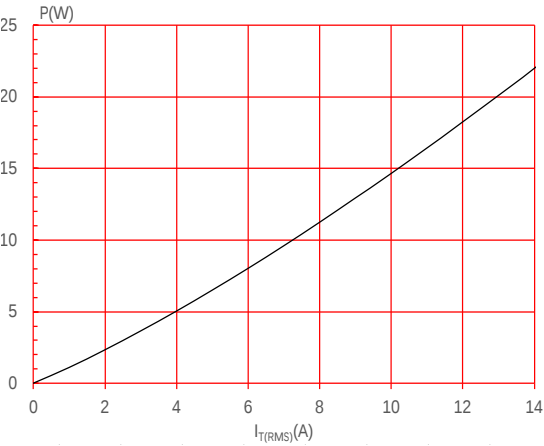
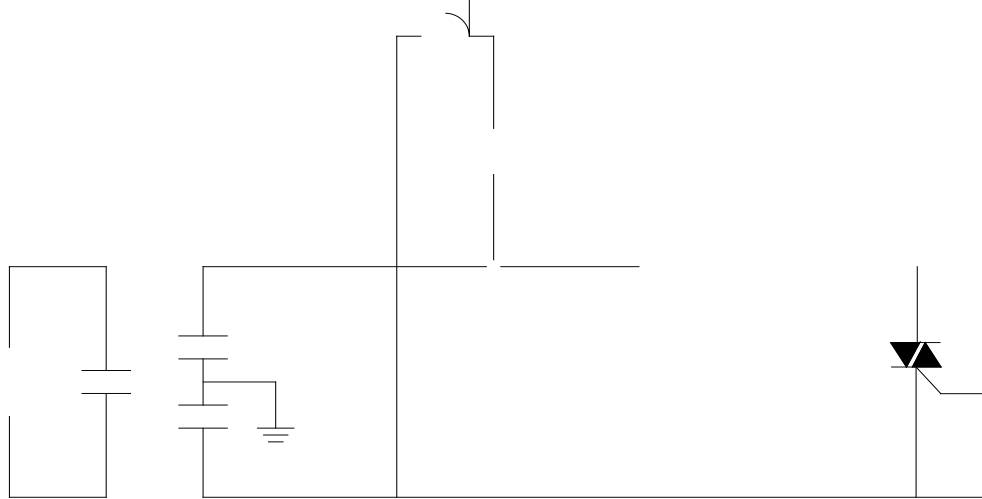


FIG.3: Surge peak on-state current versus TJ

FIG.2: RMS on-state current versus case temperature

TJ 0 56.711:

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



Information furnished in this document is believed to be accurate and reliable. However,
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